AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 6 with the following amended paragraph:

This application is related to <u>U.S. Application No. 10/080,012</u>, filed February 20, 2002, which is herein incorporated in its entirety by reference. Chang et al., co-filed U.S. patent application Ser. No.: _____attorney docket No.:CDDC/CHC/002. To the extent not repeated herein, the contents of Cheng et al., are incorporated herein by reference.

Please add the following new paragraph before the paragraph beginning on page 7, line 24:

Fig. 5 is a cross-sectional structural view of another embodiment of the core of an electron-emitting device provided with a seed layer in accordance with the present invention.

Please replace the paragraph beginning on page 10, line 30 with the following amended paragraph:

Fig. 3A depicts a partial cross-sectional representation of the field emitter structure 1 of one embodiment of the present invention. The method of fabricating the field emitter structure 1 generally includes providing a [[bas]] base plate 100 and disposing thereon a plurality of emitter electrodes. The group of generally parallel emitter electrodes 110 are situated on base plate baseplate 100.

Please replace the paragraph beginning on page 16, line 17 with the following amended paragraph:

Fig. 5 illustrates an embodiment of the invention in which the dielectric layer comprises a dual layer. As Fig. 5 illustrates In one embodiment of the present invention, the dielectric strips 152 comprises two layers 126 and 127, which in one embodiment are formed of silicon dioxide and silicon nitride having a thickness of $0.5 - 2.0 \mu m$. In another embodiment, dielectric layer

strips 125 comprises comprise of a single layer of silicon-oxy-nitride having a thickness of $0.5 - 2.0 \mu m$.